

MICRO ELECTRONICS

查询2N5232供应信息

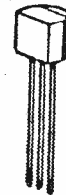
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2N5232

NPN SILICON TRANSISTOR

2N5232 is NPN silicon planar transistor use in general purpose applications.

TO-92B



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	50V
Collector-Base Voltage	V _{CB0}	70V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current	I _C	100mA
Total Power Dissipation	P _{tot}	330mW
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO}	50		V	I _C =10mA I _B =0
Collector-Base Breakdown Voltage	BV _{CB0}	70		V	I _C =100μA I _E =0
Emitter-Base Breakdown Voltage	BV _{EB0}	5		V	I _E =100μA I _C =0
Collector Cutoff Current	I _{CBO}		30	nA	V _{CB} =50V I _E =0
Collector Cutoff Current	I _{CS}		30	nA	V _{CB} =50V V _{EB} =0
Emitter Cutoff Current	I _{EB0}		50	nA	V _{EB} =5V I _C =0
D.C. Current Gain	h _{FE}	250	500		I _C =2mA V _{CE} =10V
Base-Emitter Voltage	V _{BE}		0.9	V	I _C =2mA V _{CE} =10V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	0.12		V	I _C =10mA I _B =1mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.78		V	I _C =10mA I _B =1mA
Output Capacitance	C _{ob}		4	pF	V _{CB} =10V f=1MHz

